

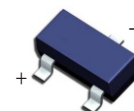
SMD Switching Diode



SMD Diodes Specialist

CDSV3-19-G/20-G/21-G

High Speed
RoHS Device



Features

- Fast switching diode.
- Surface mount package ideally for automatic insertion.
- For general purpose switching applications.
- High conductance.

Mechanical data

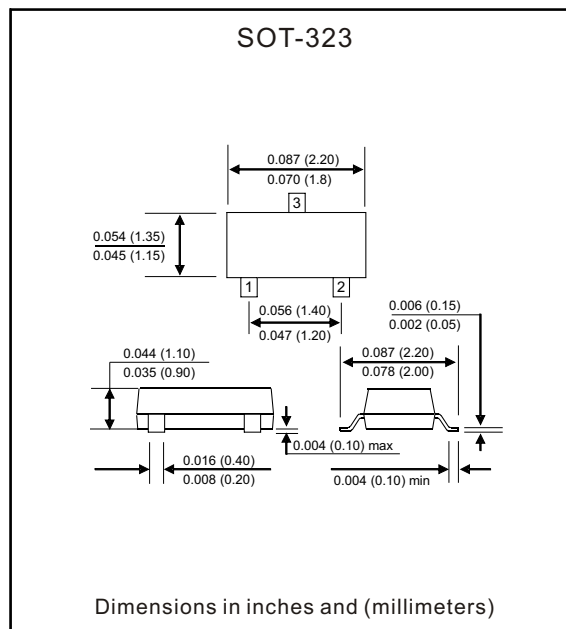
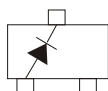
Case: SOT-323

Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.

Marking: CDSV3-19-G KA8

CDSV3-20-G KT2

CDSV3-21-G KT3



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Power dissipation	P _D	200	mW
Collector current	I _F	200	mA
Collector-base voltage	V _R	CDSV3-19-G: 120 CDSV3-20-G: 150 CDSV3-21-G: 200	V
Junction and storage temperature	T _J , T _{STG}	-55 ~ +150	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	V _{(BR)R}	I _R =100uA	100 150 200		V
Reverse leakage current	I _R	V _R =100V V _R =150V V _R =200V		0.1	uA
Forward voltage	V _F	I _F =100mA I _F =200mA		1 1.25	V
Diode capacitance	C _D	V _R =0V, f=1MHz		5	pF
Reverse recovery time	t _{rr}	I _F =I _R =30mA, I _{rr} =0.1xI _R		50	nS

Characteristic Curves (CDSV3-19-G/20-G/21-G)

Fig. 1 - Forward Characteristics

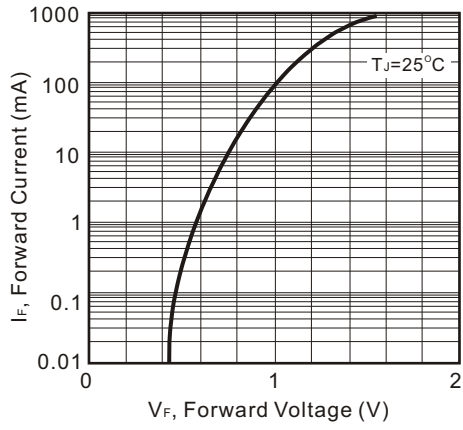


Fig. 2 - Leakage Current vs Junction Temperature

